



REPLACEMENT SHEET
Method of Making Relaxed Silicon-Germanium on Insulator via Layer Transfer with Stress Reduction
Serial No.: 10/677,005
Jer-shen Maa; Jong-Jan Lee; Douglas James Tweet; Sheng Teng Hsu
1/8

Fig. 1

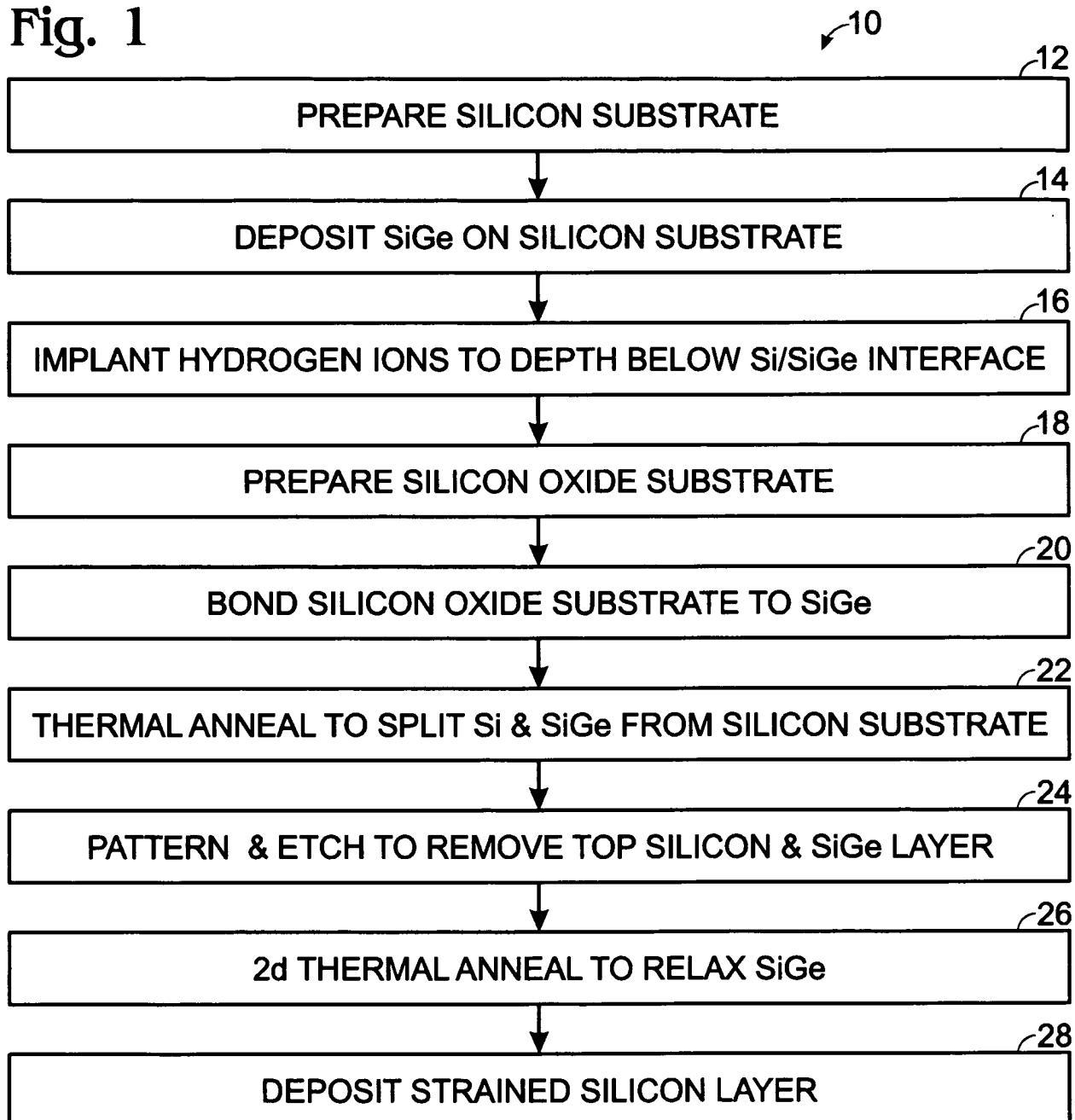


Fig. 2



Fig. 3

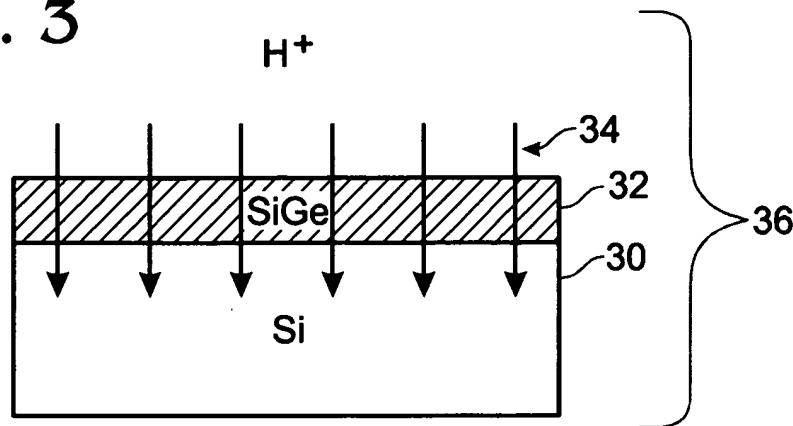


Fig. 4

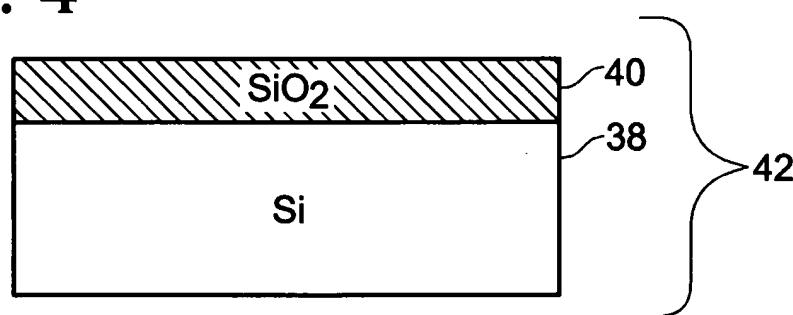


Fig. 5

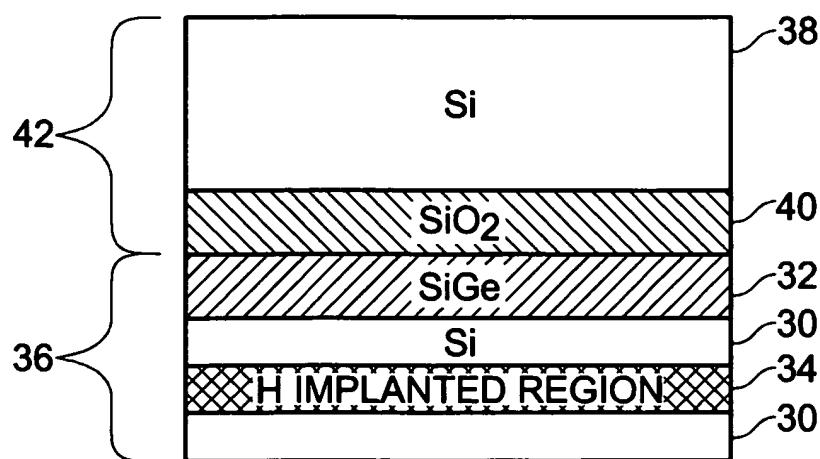


Fig. 6

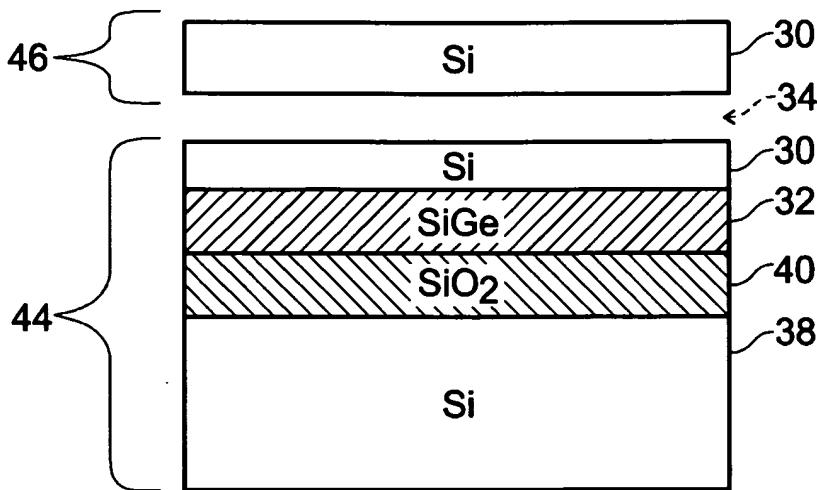


Fig. 7

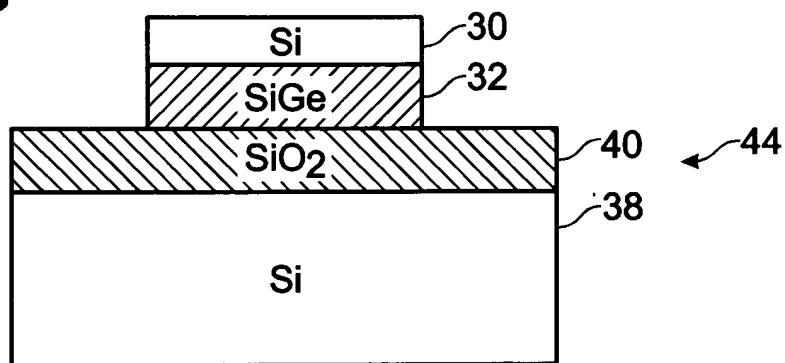


Fig. 8

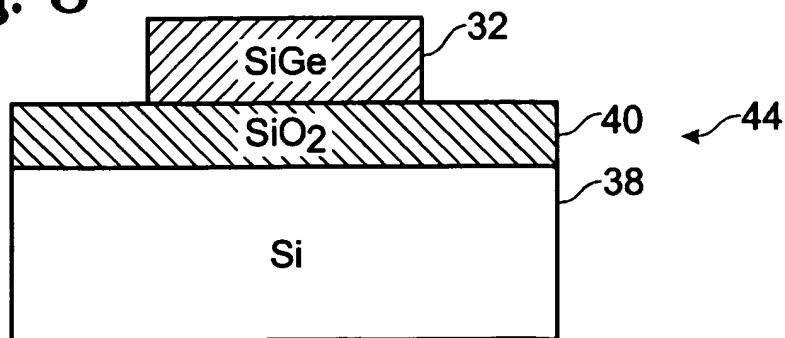


Fig. 9

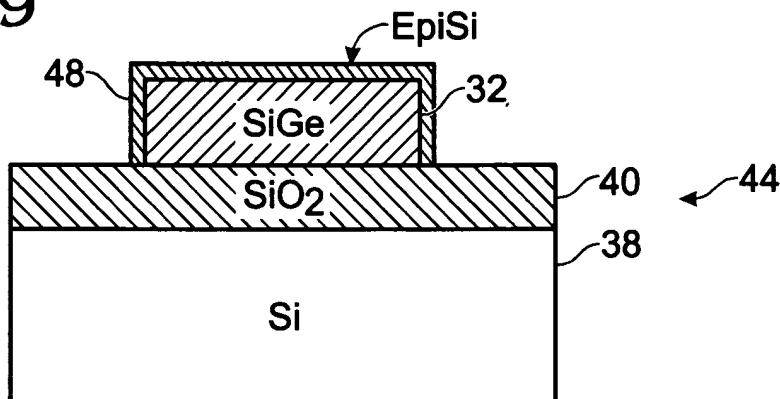


Fig. 10

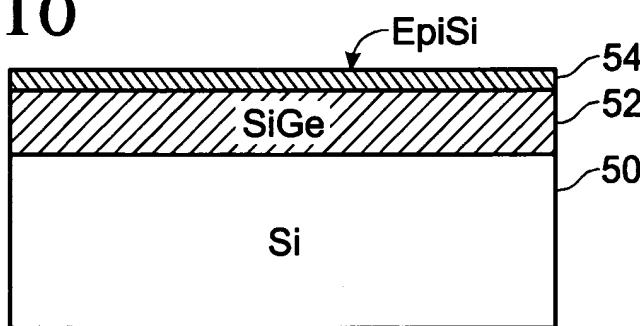


Fig. 11

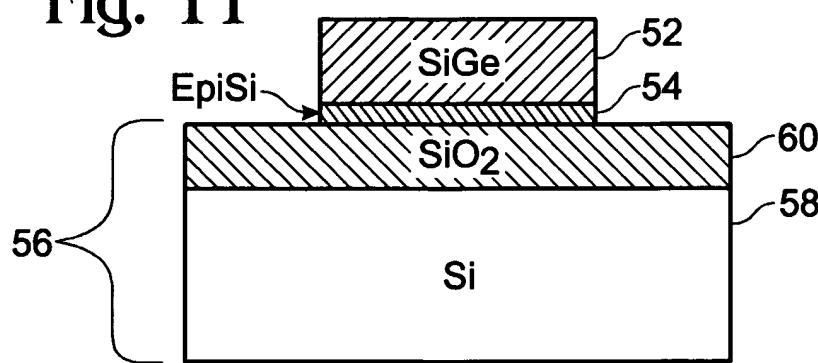
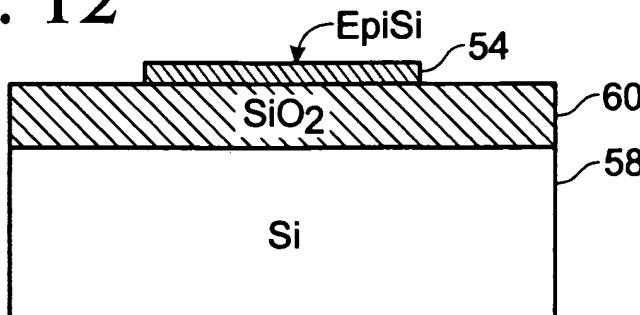


Fig. 12



REPLACEMENT SHEET

Method of Making Relaxed Silicon-Germanium on Insulator via Layer Transfer with Stress Reduction

Serial No.: 10/677,005

Jer-shen Maa; Jong-Jan Lee; Douglas James Tweet; Sheng Teng Hsu

5/8

Fig. 13

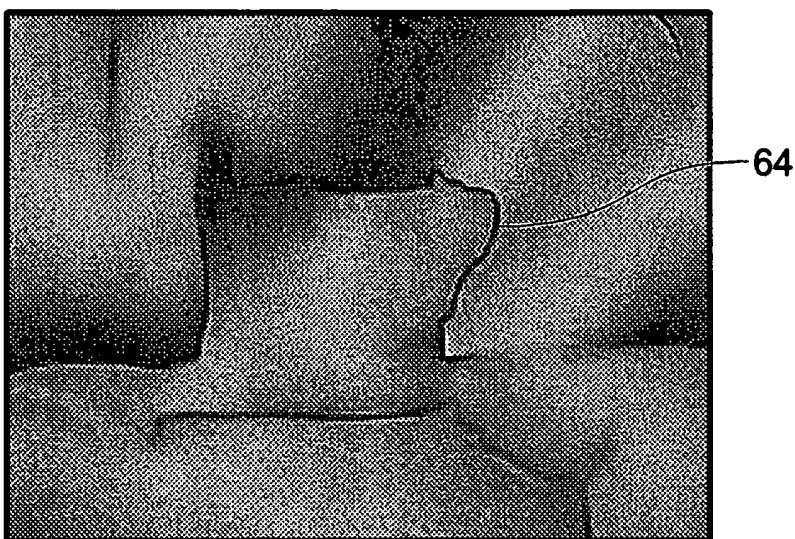


Fig. 14

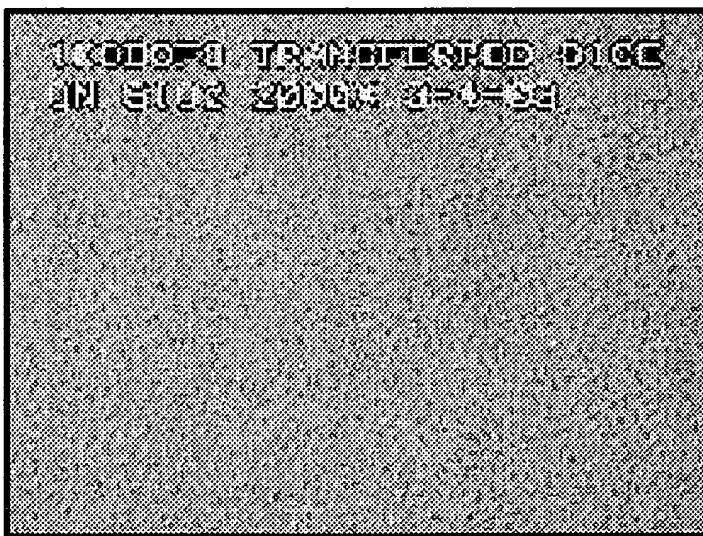


Fig. 16

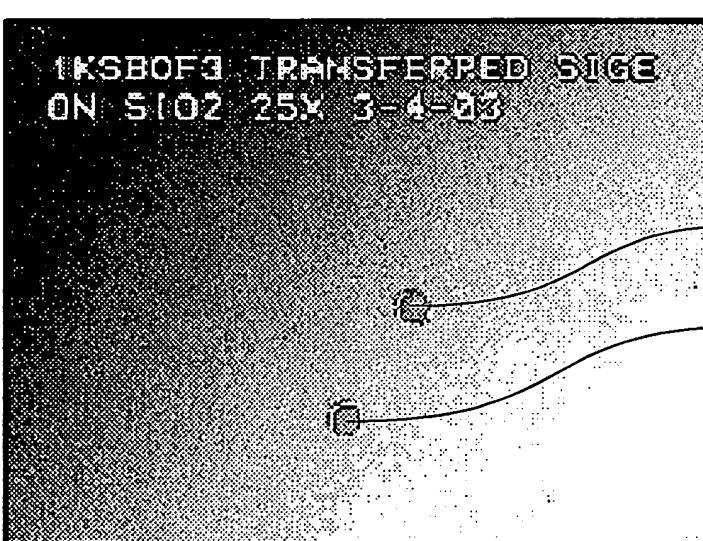


Fig. 15

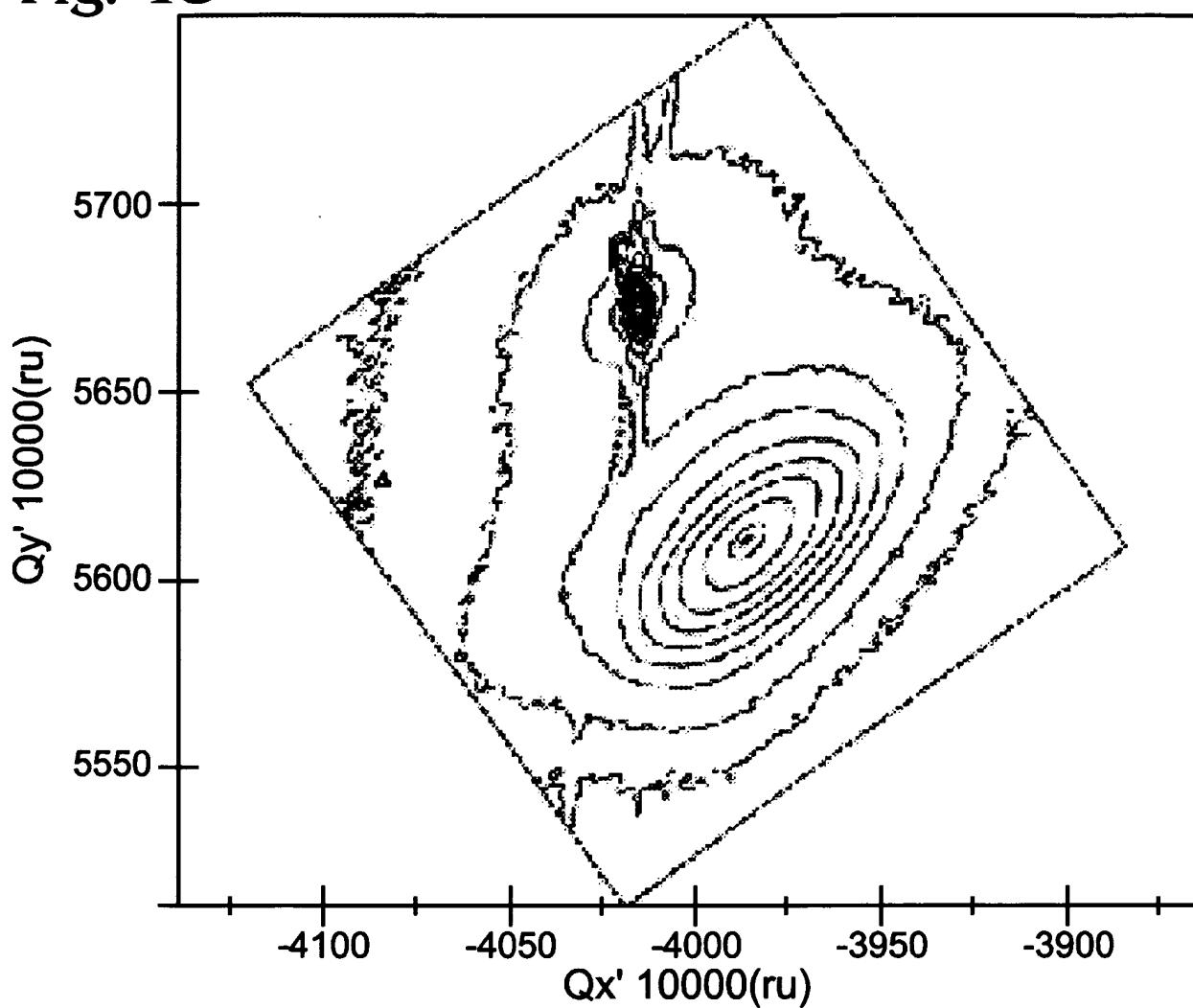
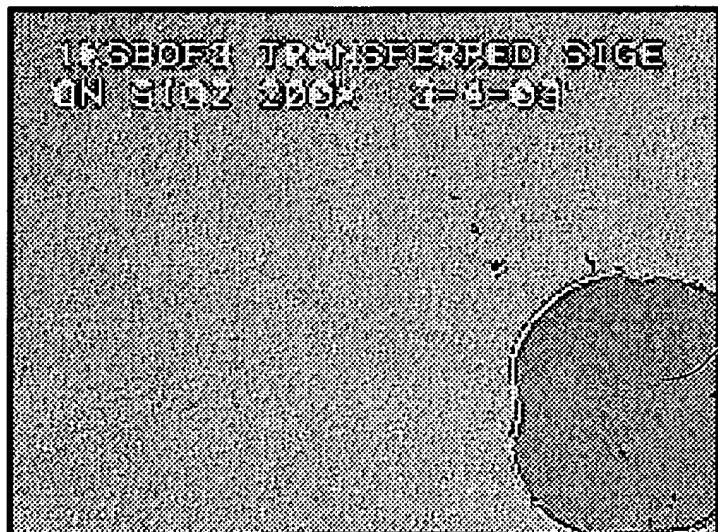


Fig. 17



REPLACEMENT SHEET

Method of Making Relaxed Silicon-Germanium on Insulator via Layer Transfer with Stress Reduction

Serial No.: 10/677,005

Jer-shen Maa; Jong-Jan Lee; Douglas James Tweet; Sheng Teng Hsu

7/8

Fig. 18

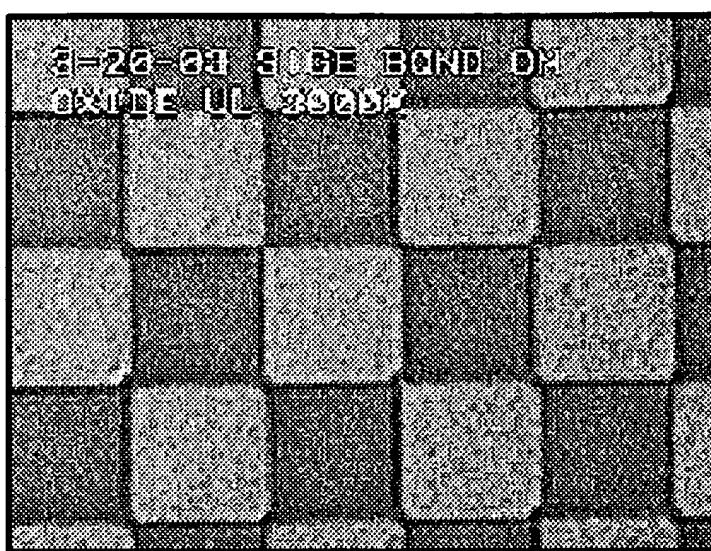


Fig. 19

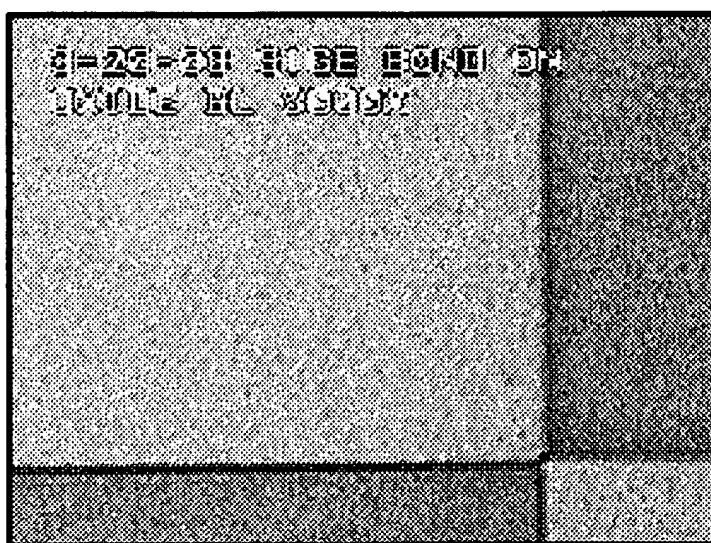
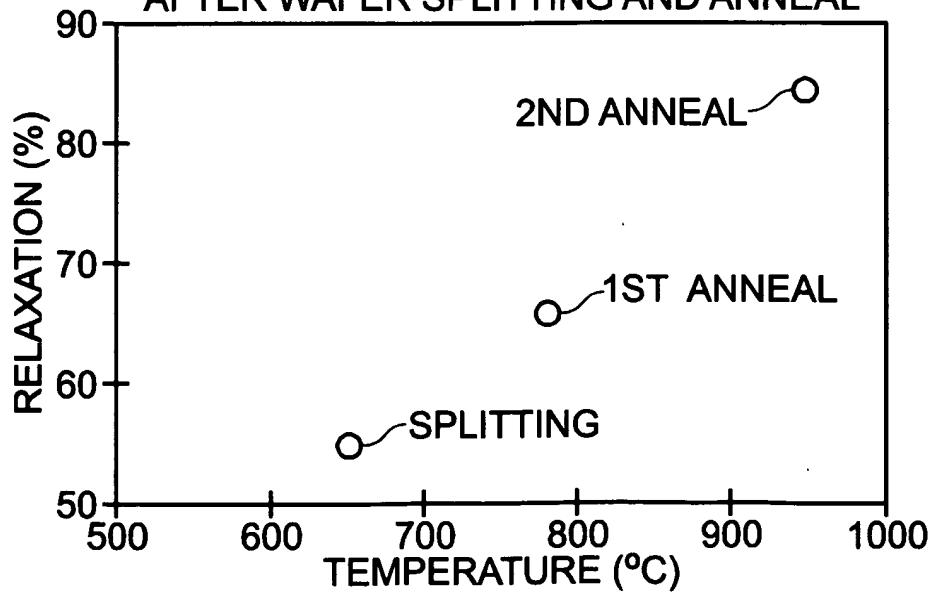


Fig. 20

RELAXATION OF SiGe ON SiO₂
AFTER WAFER SPLITTING AND ANNEAL



REPLACEMENT SHEET

Method of Making Relaxed Silicon-Germanium on Insulator via Layer Transfer with Stress Reduction

Serial No.: 10/677,005

Jer-shen Maa; Jong-Jan Lee; Douglas James Tweet; Sheng Teng Hsu

8/8

Fig. 21

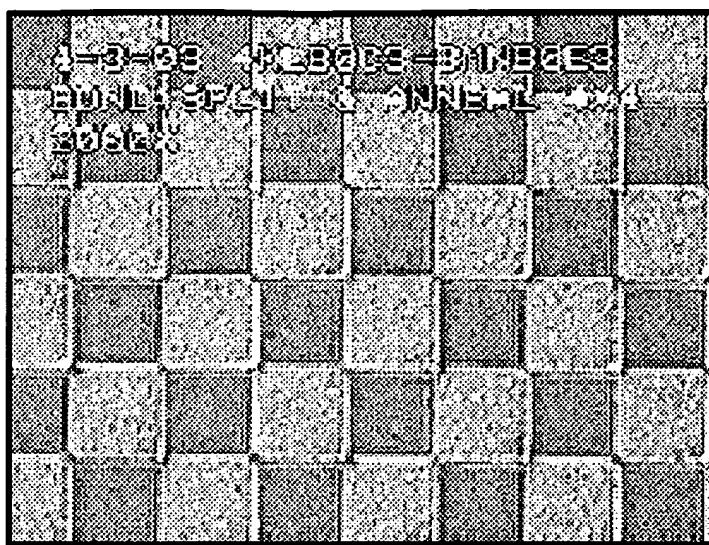


Fig. 22

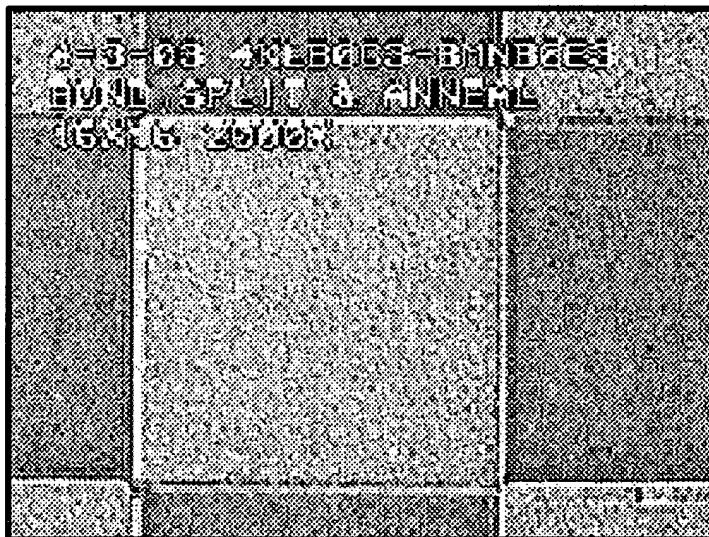


Fig. 23

